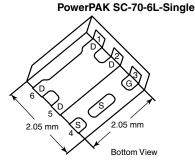


N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$ (Max.)	I _D (A) ^a	Q _g (Typ.)						
40	0.026 at V _{GS} = 10 V	12							
	0.028 at V _{GS} = 4.5 V	12	6.9 nC						
	0.029 at V _{GS} = 3.7 V	12	0.9110						
	0.035 at V _{GS} = 2.5 V	12							



Ordering Information:

SiA440DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- TrenchFET® Power MOSFET
- 100 % R_{α} and UIS Tested

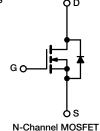




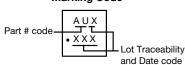
HALOGEN FREE

APPLICATIONS

- · Portable Devices such as Tablet PCs and Mobile Computing
 - DC/DC Converter
 - Boost Converter
 - Load Switch
 - Power Management
 - LED Backlighting



Marking Code



Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	40	V
Gate-Source Voltage		V _{GS}	± 12	v
	T _C = 25 °C		12 ^a	
Continuous Drain Current /T 150 °C\	T _C = 70 °C		12 ^a	
Continuous Drain Current (T _J = 150 °C)	T _A = 25 °C	I _D	8.6 ^{a,b, c}	
	T _A = 70 °C		6.9 ^{b, c}	
Pulsed Drain Current (t = 100 μs)		I _{DM}	50	A
Continuous Courses Dusin Diads Coursest	T _C = 25 °C	1	12 ^a	
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	2.9 ^{b, c}	
Single Avalanche Current	L = 0.1 mH	I _{AS}	11	
Single Avalanche Energy	L = 0.1 IIIIA	E _{AS}	6	mJ
	T _C = 25 °C		19	
Manianus Davies Discipation	T _C = 70 °C	В	12	10/
Maximum Power Dissipation	T _A = 25 °C	P _D	3.5 ^{b, c}	w
	T _A = 70 °C		2.2 ^{b, c}	
Operating Junction and Storage Temperature Ra	ange	T _J , T _{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature	e) ^{d, e}		260	

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient ^{b, f} t ≤		R_{thJA}	28	36	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R _{thJC}	5.3	6.5	O/ VV				

Notes:

- a. Based on package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- $d. \ See \ solder \ profile \ (\underline{www.vishay.com/doc?73257}). \ The \ PowerPAK \ SC-70 \ is \ a \ leadless \ package. \ The \ end \ of \ the \ lead \ terminal \ is \ exposed \ copper \ package.$ (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	40			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	J 050 ·· A		39		1400
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	$I_D = 250 \mu A$		- 3.6		mV/°C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.6		1.4	٧
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA
Zana Oaka Walka na Burin Oannani		$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$			1	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α
	, ,	V _{GS} = 10 V, I _D = 9 A		0.021	0.026	
_		$V_{GS} = 4.5 \text{ V}, I_D = 7 \text{ A}$		0.022	0.028	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 3.7 \text{ V}, I_D = 7 \text{ A}$		0.023	0.029	
	=	$V_{GS} = 2.5 \text{ V}, I_D = 7 \text{ A}$		0.026	0.035	
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 9 A		45		S
Dynamic ^b	0	20 2		L		
Input Capacitance	C _{iss}			700		pF
Output Capacitance	C _{oss}	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		87		
Reverse Transfer Capacitance	C _{rss}	20 4 40		40		
·		$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 9 \text{ A}$		14.3	21.5	nC
Total Gate Charge	Q_g	20 1 00 1 2		6.9	10.5	
Gate-Source Charge	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 9 \text{ A}$		1.4		
Gate-Drain Charge	Q_{gd}			2		
Gate Resistance	R_g	f = 1 MHz	0.2	1	2	Ω
Turn-On Delay Time	t _{d(on)}			7	15	
Rise Time	t _r	V_{DD} = 20 V, R_L = 2.9 Ω		5	10	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 7 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		20	40	
Fall Time	t _f			3	10	
Turn-On Delay Time	t _{d(on)}			12	25	ns
Rise Time	t _r	V_{DD} = 20 V, R_L = 2.9 Ω		32	65	
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 7 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		23	45	
Fall Time	t _f			5	10	
Drain-Source Body Diode Characteristic	s					
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			12	A
Pulse Diode Forward Current (t = 100 μs)	I _{SM}				50	
Body Diode Voltage	V_{SD}	I _S = 7 A		0.85	1.2	V
Body Diode Reverse Recovery Time	t _{rr}			15	30	ns
Body Diode Reverse Recovery Charge	Q _{rr}	L = 7 A dl/dt = 100 A/··· T = 05 °C		7.5	15	nC
Reverse Recovery Fall Time	ta	$I_F = 7 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		9		
Reverse Recovery Rise Time	t _b			6		ns

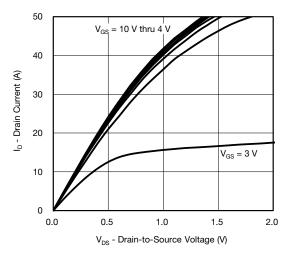
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

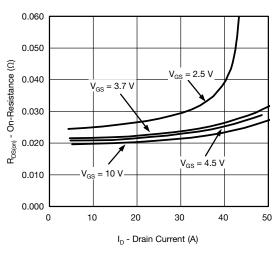
b. Guaranteed by design, not subject to production testing.



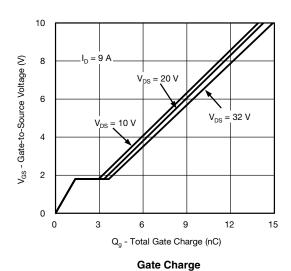
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

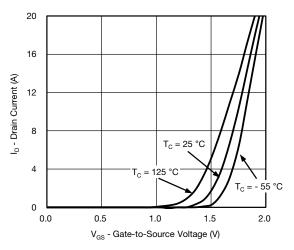


Output Characteristics

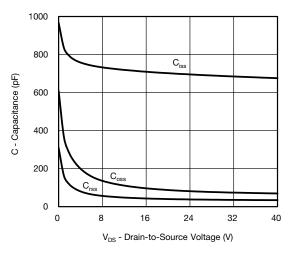


On-Resistance vs. Drain Current and Gate Voltage

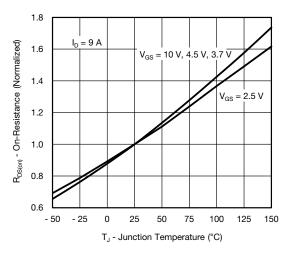




Transfer Characteristics

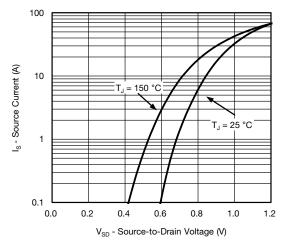


Capacitance

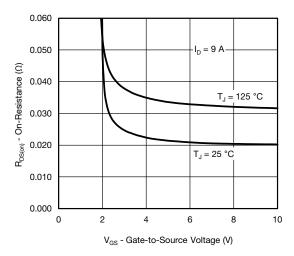


On-Resistance vs. Junction Temperature

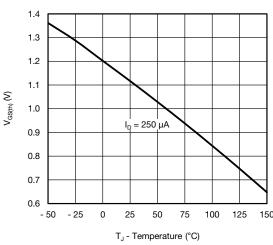
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



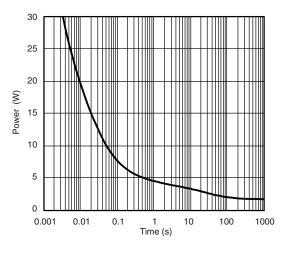
Source-Drain Diode Forward Voltage



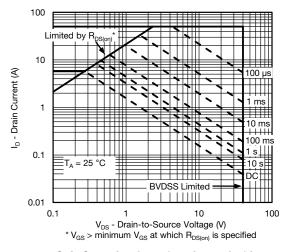
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



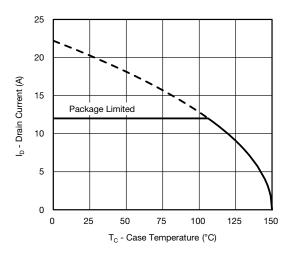
Single Pulse Power, Junction-to-Ambient



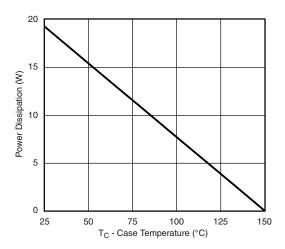
Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Current Derating*

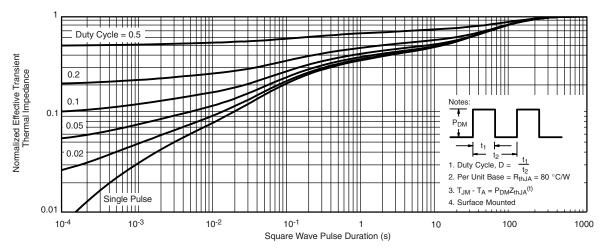


Power, Junction-to-Case

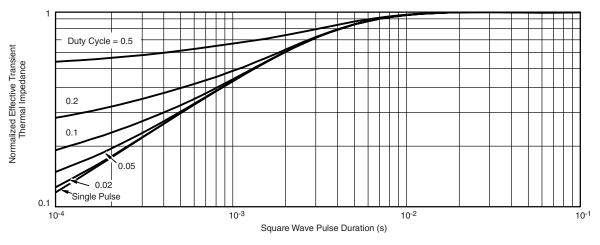
 $^{^{\}star}$ The power dissipation P_D is based on $T_{J(max.)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



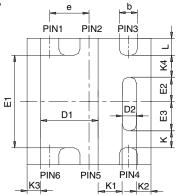
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?64138.





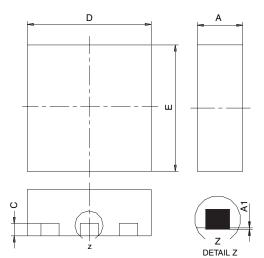
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

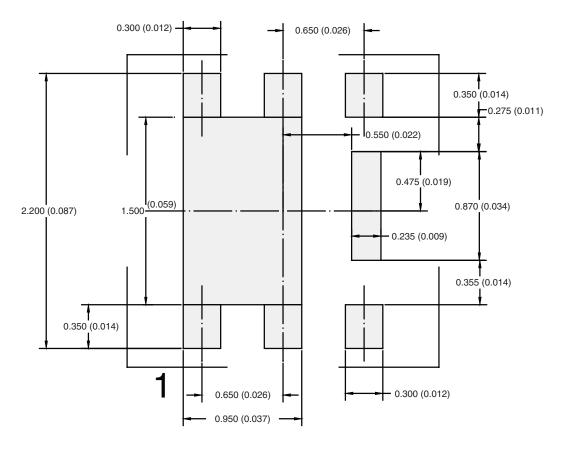
	SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP	١		0.011 TYP		0.275 TYP			0.011 TYP		
K1		0.400 TYP	١	0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP 0.009 TYP			0.252 TYP 0.010 TYP							
К3		0.225 TYP	1	0.009 TYP								
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006
FCN: C-07431 – Bey C. 06-Aug-07												

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

Return to Index

ATTLICATION NOT



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Revision: 13-Jun-16 1 Document Number: 91000

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

Vishay:

SIA440DJ-T1-GE3